

## Amendments to the Claims

This listing of claims will replace all prior versions, and listings, of claims in the application:

### Listing of Claims

~~1.~~ 1-16 (canceled).

~~17.~~ (New) A semiconductor device comprising:

a semiconductor substrate optionally personalized with electronic devices formed thereon;

at least one copper interconnect pad formed on said substrate; and

a layer of a zinc complex formed on said at least one interconnect pad, wherein said complex comprises:

copper ion,

zinc ion,

an organic acid and

an azole.

~~18.~~ (New) The semiconductor device, according to claim ~~17~~<sup>1</sup>, wherein said zinc complex further comprises a surfactant.

~~19.~~ (New) The semiconductor device, according to claim ~~17~~<sup>1</sup>, wherein said zinc complex further comprises an amine.

~~20.~~ (New) The semiconductor device, according to claim ~~17~~<sup>1</sup>, wherein said zinc complex further comprises a complexing agent.

~~21.~~ (New) The semiconductor device, according to claim ~~17~~<sup>1</sup>, wherein the molar ratio of said zinc ion to said azole is from about 1:1 to about 2:1.

~~6.~~  
~~22.~~ (New) The semiconductor device, according to claim ~~17~~<sup>1</sup>, wherein said azole is benzotriazole.

~~7.~~  
~~23.~~ (New) The semiconductor device, according to claim ~~18~~<sup>2</sup>, wherein said surfactant is a nonionic surfactant.

~~8.~~  
~~24.~~ (New) The semiconductor device, according to claim ~~23~~<sup>7</sup>, wherein said surfactant is selected from the group consisting of SANDOPAN ECO and Triton DF16.

~~9.~~  
~~25.~~ (New) The semiconductor device, according to claim ~~17~~<sup>1</sup>, further comprising ammonia.

~~10.~~  
~~26.~~ (New) The semiconductor device, according to claim ~~20~~<sup>44</sup>, wherein said complexing agent is triethanolamine.

~~11.~~  
~~27.~~ (New) The semiconductor device, according to claim ~~17~~<sup>1</sup>, wherein said organic acid is acetic acid.

~~12.~~  
~~28.~~ (New) The semiconductor device, according to claim ~~17~~<sup>1</sup>, wherein said zinc complex layer is deposited from a solution comprising:

at least one azole present at a concentration of from about 0.001 to about 0.5 molar;

a zinc salt having present at a concentration of from about 0.1 to about 1 molar;

an organic acid; and

a complexing agent, and wherein

the pH of said solution is from about 5 to about 8.

~~13.~~  
~~29.~~ (New) The semiconductor device, according to claim ~~17~~<sup>1</sup>, further comprising a layer of a solder applied to said zinc complex layer.